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516a/M3Arti /



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			±		

FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)

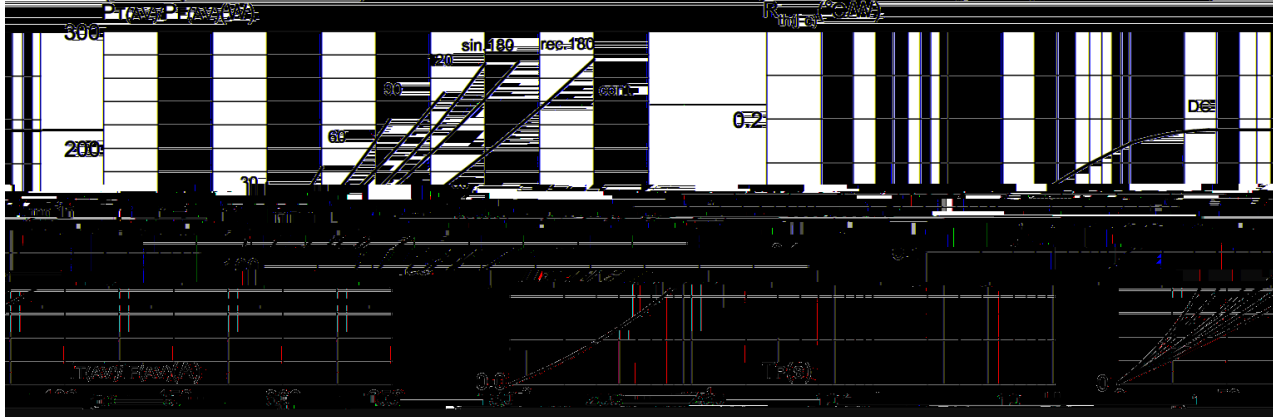


FIG.2: Maximum transient thermal impedance
junction to case (per thyristor or diode)

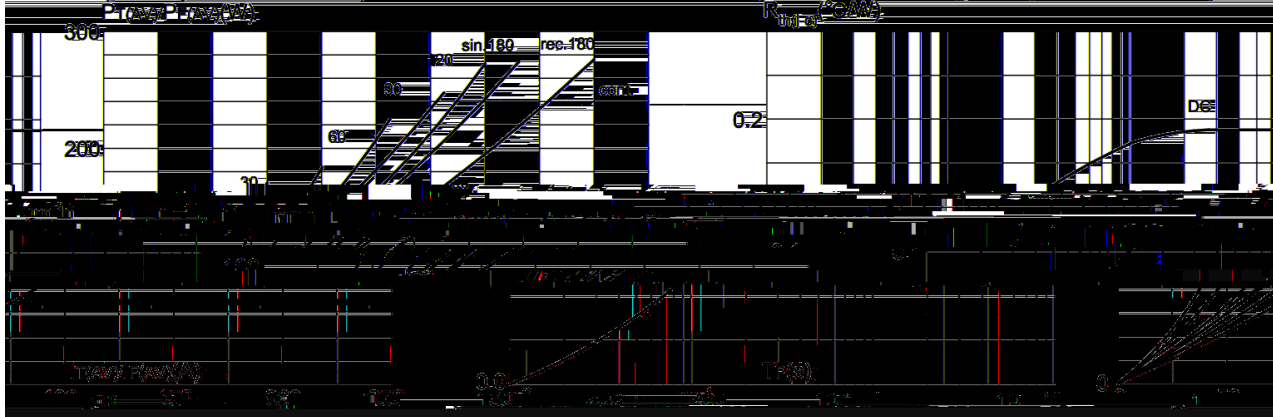


FIG.5 Gate trigger characteristics

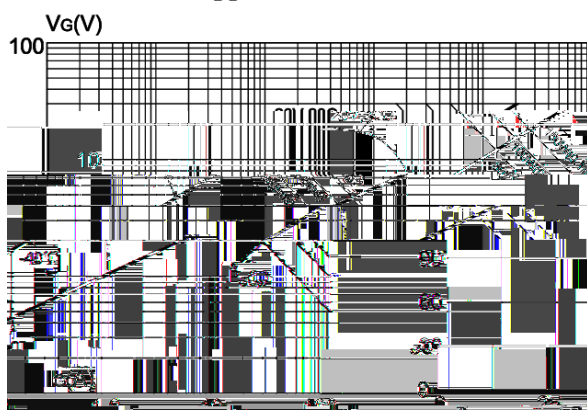


FIG.6: Forward current vs. case temperature
I_{F(AV)}(A) (per thyristor or diode)

